NPN Silicon General Purpose Amplifier Transistor

2SC4617G, S2SC4617G

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SC−75/SOT-416 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Reduces Board Space
- High h_{FE}, 210−460 (typical)
- Low $V_{CE(sat)}$, < 0.5 V
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS (T_J = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{(BR)CBO}$	50	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	5.0	Vdc
Collector Current − Continuous	I_C	100	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

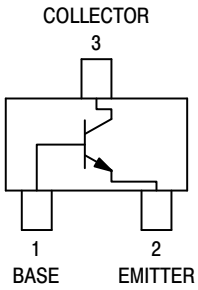
Characteristic	Symbol	Max	Unit
Power Dissipation (Note 1)	P_D	125	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	−55 ~ +150	°C

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

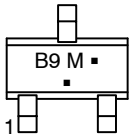
*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT

SC−75
CASE 463−01
STYLE 1



MARKING DIAGRAM



B9 = Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
2SC4617G	SC−75 (Pb−Free)	3,000/Tape & Reel
S2SC4617G	SC−75 (Pb−Free)	3,000/Tape & Reel
2SC4617T1G	SC−75 (Pb−Free)	3,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage (I_C = 50 μAdc, I_E = 0)	$V_{(BR)CBO}$	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	50	–	–	Vdc
Emitter-Base Breakdown Voltage (I_E = 50 μAdc, I_E = 0)	$V_{(BR)EBO}$	5.0	–	–	Vdc
Collector-Base Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	–	–	0.5	μA
Emitter-Base Cutoff Current (V_{EB} = 4.0 Vdc, I_B = 0)	I_{EBO}	–	–	0.5	μA
Collector-Emitter Saturation Voltage (Note 2) (I_C = 60 mAdc, I_B = 5.0 mAdc)	$V_{CE(sat)}$	–	–	0.4	Vdc
DC Current Gain (Note 2) (V_{CE} = 6.0 Vdc, I_C = 1.0 mAdc)	h_{FE}	120	–	560	–
Transition Frequency (V_{CE} = 12 Vdc, I_C = 2.0 mAdc, f = 30 MHz)	f_T	–	180	–	MHz
Output Capacitance (V_{CB} = 12 Vdc, I_C = 0 Adc, f = 1 MHz)	C_{OB}	–	2.0	–	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

TYPICAL ELECTRICAL CHARACTERISTICS

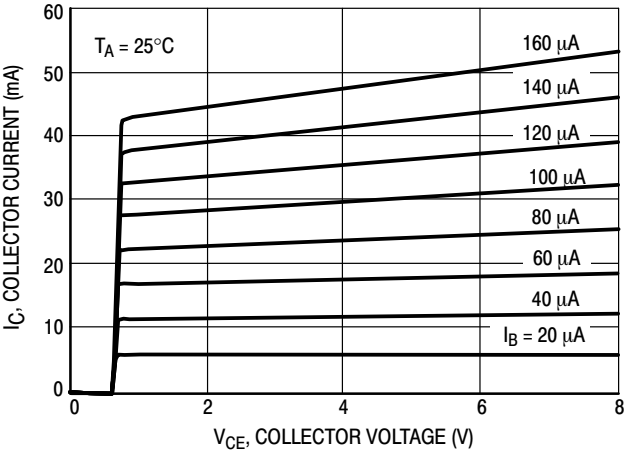


Figure 1. $I_C - V_{CE}$

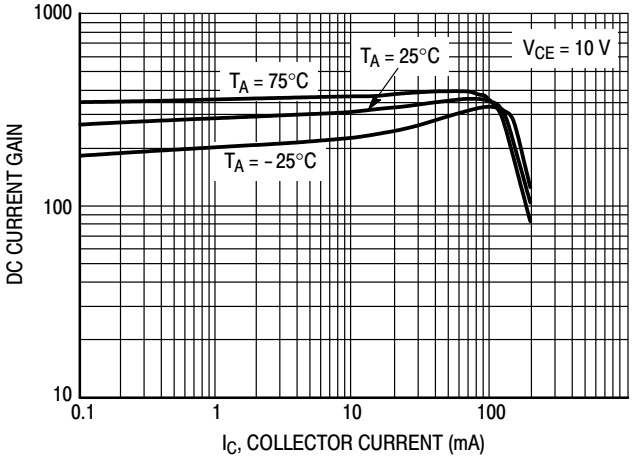


Figure 2. DC Current Gain

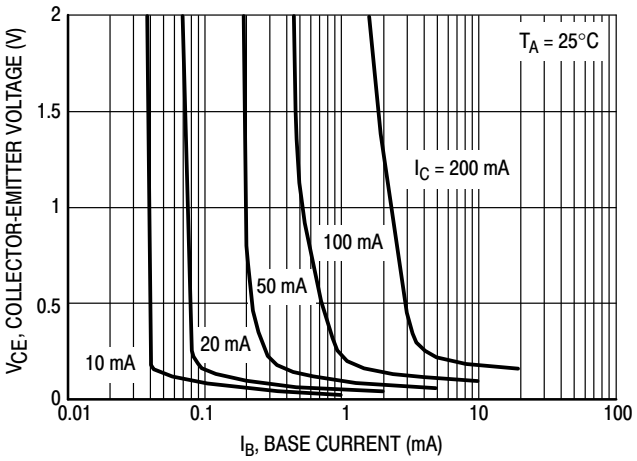


Figure 3. Collector Saturation Region

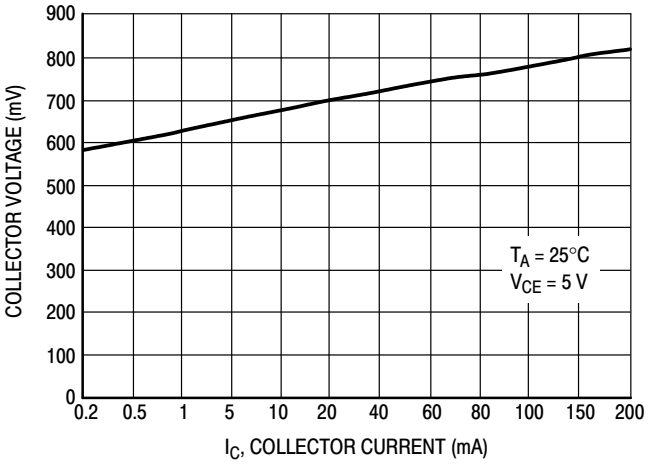


Figure 4. On Voltage

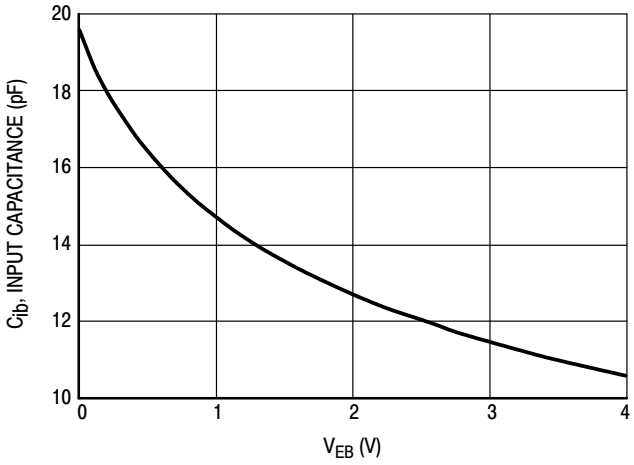


Figure 5. Capacitance

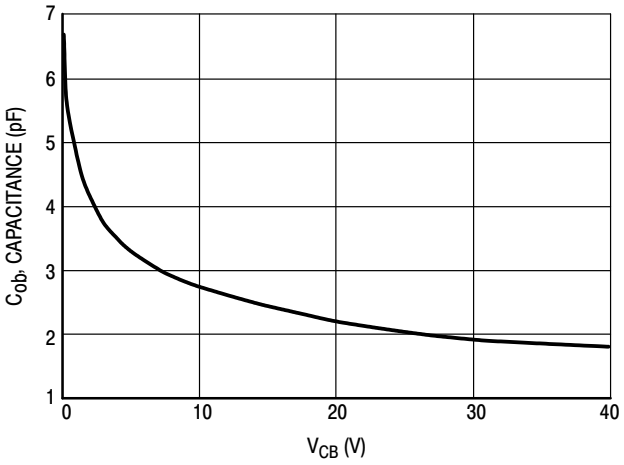
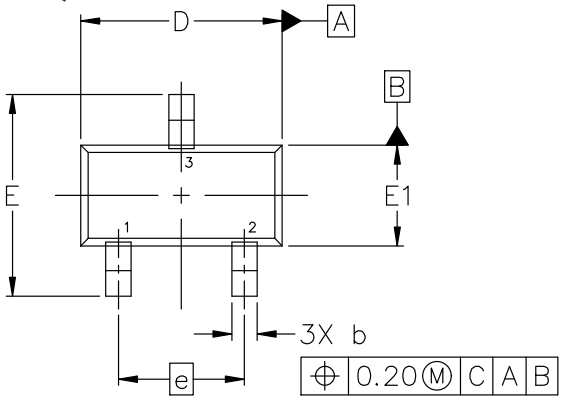


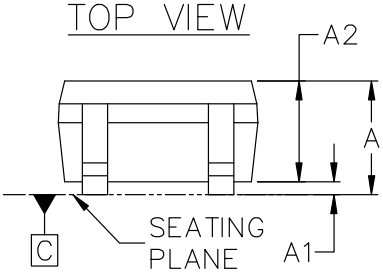
Figure 6. Capacitance

SC75−3 1.60x0.80x0.80, 1.00P
CASE 463
ISSUE H

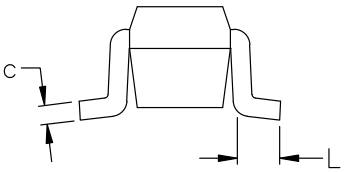
DATE 01 FEB 2024



TOP VIEW



SIDE VIEW



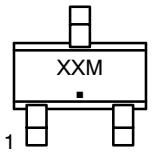
END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.70	0.80	0.90
A1	0.00	0.05	0.10
A2		0.80 REF.	
b	0.15	0.20	0.30
c	0.10	0.15	0.25
D	1.55	1.60	1.65
E	1.50	1.60	1.70
E1	0.70	0.80	0.90
e		1.00 BSC	
L	0.10	0.15	0.20

GENERIC
MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

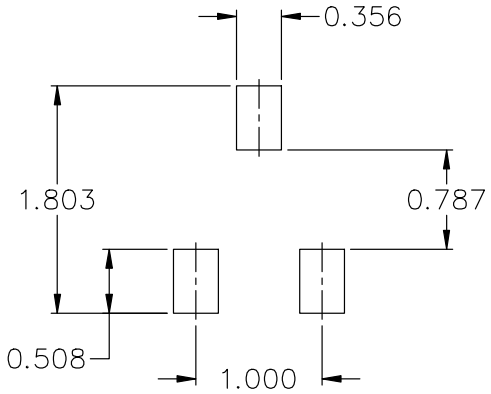
STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 2:
PIN 1. ANODE
2. N/C
3. CATHODE

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. GATE
2. SOURCE
3. DRAIN



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

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DESCRIPTION:	SC75−3 1.60x0.80x0.80, 1.00P	PAGE 1 OF 1

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